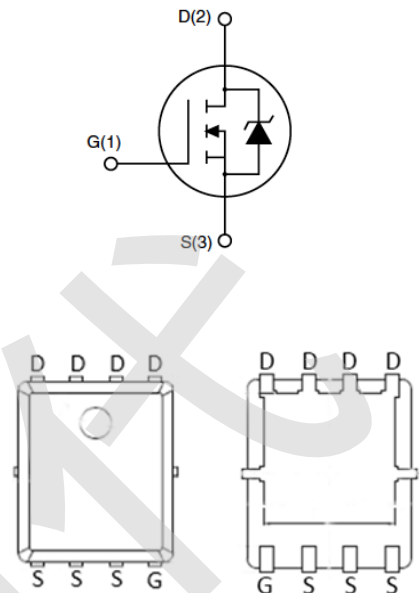


Feature

- 100V,90A
 $R_{DS(ON)} < 7.7m\Omega @ V_{GS}=10V$ (TYP:6.4m Ω)
 $R_{DS(ON)} < 10m\Omega @ V_{GS}=4.5V$ (TYP:8.0m Ω)
- Split Gate Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge

Application

- PWM applications
- Load Switch
- Power management



PDFN5X6-8L

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G077N01G	APG077N01G	PDFN5*6-8L	-	-	5000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^{\circ}C$)	I_D	90	A
Continuous Drain Current ($T_a=100^{\circ}C$)	I_D	60	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	360	A
Singel Pulsed Avalanche Energy ⁽²⁾	E_{AS}	300	mJ
Power Dissipation	P_D	105	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.2	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

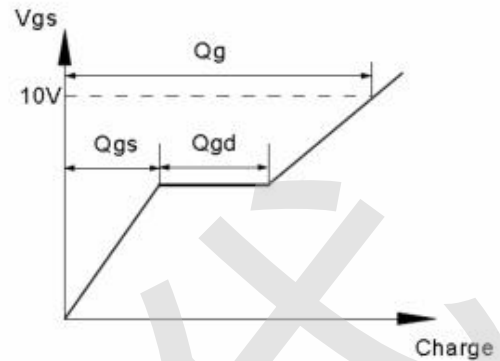
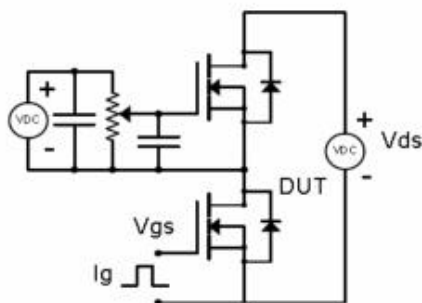
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	100	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =100V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ± 20V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.5	2.0	3.0	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =10V, I _D =40A	-	6.7	8.2	mΩ
		V _{GS} =4.5V, I _D =40A	-	8.0	10	mΩ
Forward Threshold Voltage	g _{fs}	V _{DS} =10V, I _D =40A	-	65	-	S
Gate Resistance	R _g	V _{DS} =V _{GS} =0V, f =1MHz	-	1.3	-	Ω
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f =1MHz	-	3000	-	pF
Output Capacitance	C _{oss}		-	362	-	
Reverse Transfer Capacitance	C _{rss}		-	11	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =50V, I _D =40A, V _{GS} =10V, R _G =3Ω	-	13	-	ns
Turn-on rise time	t _r		-	35	-	
Turn-off delay time	t _{d(off)}		-	20	-	
Turn-off fall time	t _f		-	15	-	
Total Gate Charge	Q _g	V _D S=50V, I _D =40A, V _G S=10V	-	30	-	nC
Gate-Source Charge	Q _{gs}		-	10	-	
Gate-Drain Charge	Q _{gd}		-	8	-	
Reverse Recovery Chrage	Q _{rr}	I _F =40A,di/dt=100A/us		90		nC
Reverse Recovery Time	T _{rr}	I _F =40A,di/dt=100A/us		60		ns
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =20A	-	-	1.3	V
Diode Forward current ⁽⁴⁾	I _S		-	-	60	A

Notes:

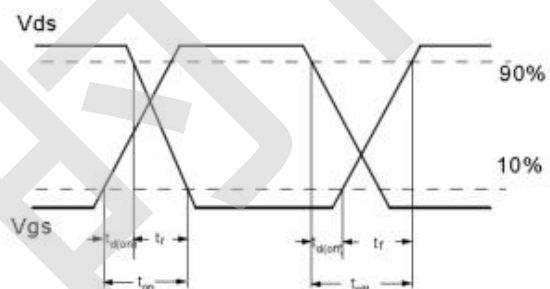
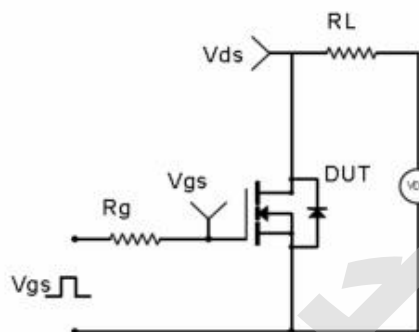
1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^{\circ}\text{C}, V_{DD} = 50V, R_G = 25\Omega, L = 0.5\text{mH}, I_{AS} = 35A$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10\text{ sec}$

Test Circuit & Waveform

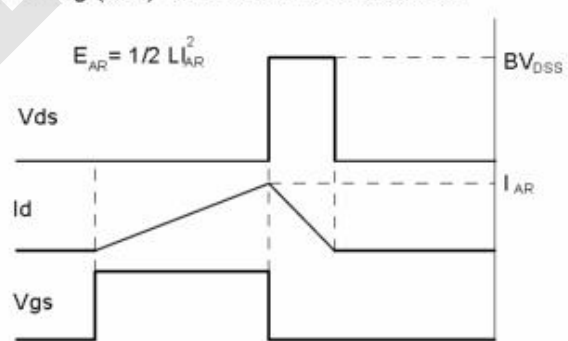
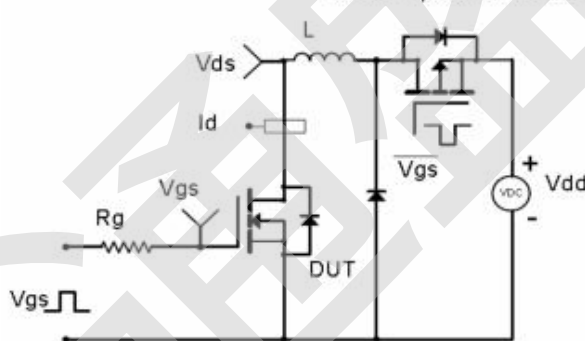
Gate Charge Test Circuit & Waveform



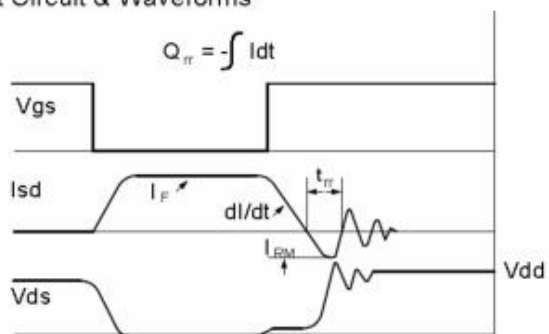
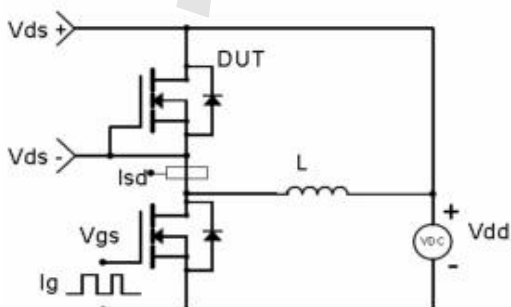
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Typical Electronic and Thermal Characteristics

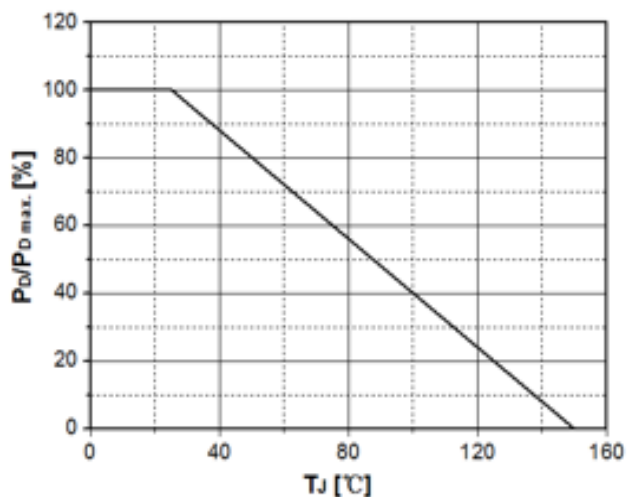


Figure 1. Power Dissipation Derating Curve

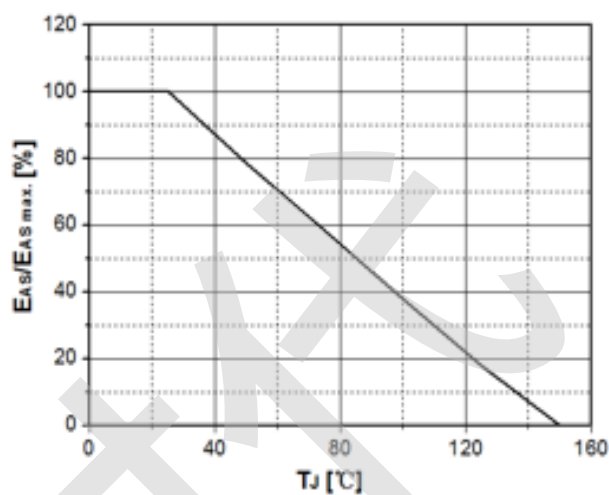


Figure 2. Avalanche Energy Derating Curve vs. Junction Temperature

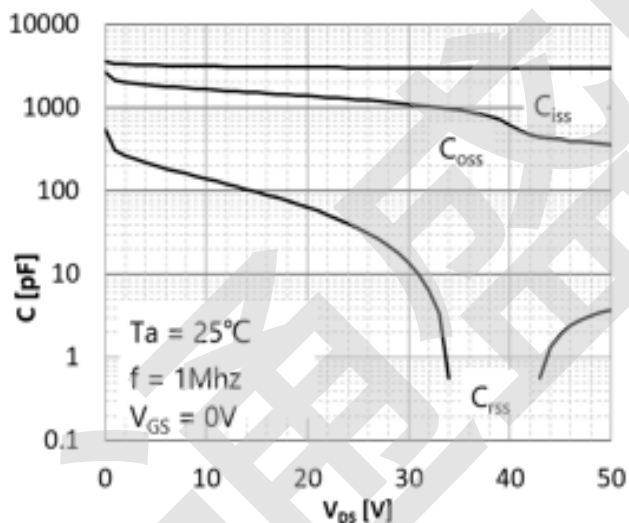


Figure 3. Capacitance Characteristics

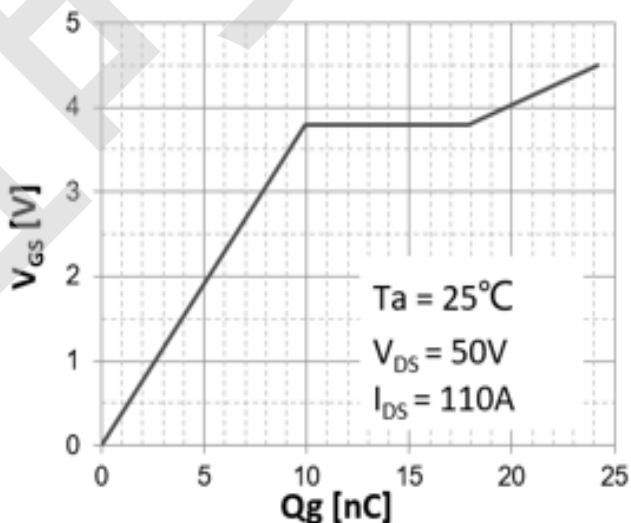
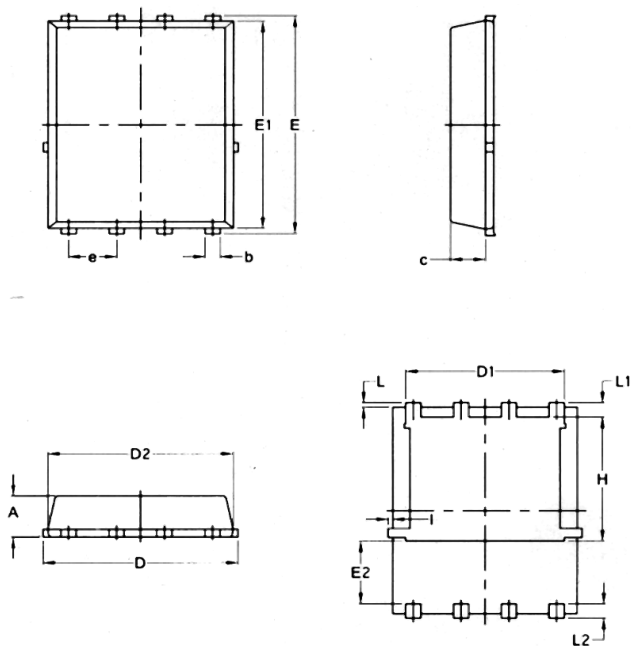


Figure 4. Gate Charge Characteristics

PDFN5*6-8L Package Information



PDFN5X6-8L

S Y M B O L	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	—	0.0630	—
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	—	0.18	—	0.0070